Si-Chen Lee

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Surface-Plasmon-Resonance Based Narrow-Bandwidth Infrared Carbon Monoxide Detection System. IEEE Sensors Journal, 2022, 22, 9803-9810.	4.7	3
2	Characteristics of Harmonic Indexes of the Arterial Blood Pressure Waveform in Type 2 Diabetes Mellitus. Frontiers in Bioengineering and Biotechnology, 2020, 8, 638.	4.1	6
3	Influence of Oxygen Molecules on Electrical Performance of Multilayer WSe2 TFT. , 2019, , .		0
4	Enhanced early immune response of leptospiral outer membrane protein LipL32 stimulated by narrow band mid-infrared exposure. Journal of Photochemistry and Photobiology B: Biology, 2019, 198, 111560.	3.8	6
5	Photoresponse of homostructure WSe2 rectifying diode. AIP Advances, 2019, 9, 075010.	1.3	10
6	Investigation of bond oscillation assisted olfactory perception by exciting the molecular chemical bonds using specific IR wavelengths. AIP Advances, 2019, 9, 075020.	1.3	2
7	Evidence of "wired―drug-cell communication through micro-barrier well-array devices. AIP Advances, 2019, 9, 095025.	1.3	1
8	Black phosphorus with a unique rectangular shape and its anisotropic properties. AIP Advances, 2018, 8, .	1.3	5
9	Current Enhancement and Bipolar Current Modulation of Top-Gate Transistors Based on Monolayer MoS2 on Three-Layer WxMo1–xS2. ACS Applied Materials & Interfaces, 2018, 10, 24733-24738.	8.0	2
10	An Uncooled LWIR-Detector With LSPR Enhancement and Selective Narrow Absorption. IEEE Photonics Technology Letters, 2018, 30, 1206-1209.	2.5	2
11	High performance MoS2 TFT using graphene contact first process. AIP Advances, 2017, 7, 085018.	1.3	4
12	Graphene/h-BN Heterostructures for Vertical Architecture of RRAM Design. Scientific Reports, 2017, 7, 9679.	3.3	29
13	A nanobiosensing method based on force measurement of antibody-antigen interaction for direct detection of enterovirus 71 by the chemically modified atomic force microscopic probe. Microbial Pathogenesis, 2017, 111, 292-297.	2.9	0
14	Waveguide resonances with selectable polarization in an infrared thermal emitter. AIP Advances, 2017, 7, 085122.	1.3	0
15	Dual-functional Memory and Threshold Resistive Switching Based on the Push-Pull Mechanism of Oxygen Ions. Scientific Reports, 2016, 6, 23945.	3.3	45
16	Triple-wavelength infrared plasmonic thermal emitter using hybrid dielectric materials in periodic arrangement. Applied Physics Letters, 2016, 109, .	3.3	11
17	Observation of "wired―cell communication over 10- <i>μ</i> m and 20- <i>μ</i> m poly(dimethylsiloxane) barriers in tetracycline inducible expression systems. Journal of Applied Physics, 2016, 119, .	2.5	4
18	Low-power resistive random access memory by confining the formation of conducting filaments. AIP Advances, 2016, 6, .	1.3	24

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19	Design and Fabrication of Nano-Structure for Three-Dimensional Display Application. IEEE Photonics Technology Letters, 2016, 28, 884-886.	2.5	5
20	A Portable Micro Gas Chromatography System for Lung Cancer Associated Volatile Organic Compound Detection. IEEE Journal of Solid-State Circuits, 2016, 51, 259-272.	5.4	58
21	The effects of narrow-band middle infrared radiation in enhancing the antitumor activity of paclitaxel. Electromagnetic Biology and Medicine, 2016, 35, 106-114.	1.4	5
22	Micron-scale ballistic thermal conduction and suppressed thermal conductivity in heterogeneously interfaced nanowires. Physical Review B, 2015, 91, .	3.2	43
23	21.5 A portable micro gas chromatography system for volatile compounds detection with 15ppb of sensitivity. , 2015, , .		3
24	Quantitative Proteomics Reveals Middle Infrared Radiation-Interfered Networks in Breast Cancer Cells. Journal of Proteome Research, 2015, 14, 1250-1262.	3.7	14
25	Low-level light therapy potentiates NPe6-mediated photodynamic therapy in a human osteosarcoma cell line via increased ATP. Photodiagnosis and Photodynamic Therapy, 2015, 12, 123-130.	2.6	41
26	Passivated graphene transistors fabricated on a millimeter-sized single-crystal graphene film prepared with chemical vapor deposition. Journal Physics D: Applied Physics, 2015, 48, 295106.	2.8	13
27	Near-unity photoluminescence quantum yield in MoS ₂ . Science, 2015, 350, 1065-1068.	12.6	993
28	Design and fabrication of birefringent nano-grating structure for circularly polarized light emission. Optics Express, 2014, 22, 7388.	3.4	11
29	Plasmonic ITO-free polymer solar cell. Optics Express, 2014, 22, A438.	3.4	17
30	Periodic anti-ring back reflectors for hydrogenated amorphous silicon thin-film solar cells. Optics Express, 2014, 22, A1128.	3.4	9
31	Fermi-level shifts in graphene transistors with dual-cut channels scraped by atomic force microscope tips. Applied Physics Letters, 2014, 104, 023511.	3.3	4
32	Double wavelength infrared emission by localized surface plasmonic thermal emitter. Applied Physics Letters, 2014, 104, 083114.	3.3	16
33	Toward epitaxially grown two-dimensional crystal hetero-structures: Single and double MoS2/graphene hetero-structures by chemical vapor depositions. Applied Physics Letters, 2014, 105, .	3.3	41
34	Experimental demonstration of <i>bindingless</i> signal delivery in human cells <i>via</i> microfluidics. Journal of Applied Physics, 2014, 116, .	2.5	4
35	The growth mechanisms of graphene directly on sapphire substrates by using the chemical vapor deposition. Journal of Applied Physics, 2014, 115, .	2.5	29
36	Field effect of in-plane gates with different gap sizes on the Fermi level tuning of graphene channels. Applied Physics Letters, 2014, 104, 183503.	3.3	0

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37	A plasmonic infrared photodetector with narrow bandwidth absorption. Applied Physics Letters, 2014, 105, .	3.3	18
38	Paper memory by all printing technology. , 2014, , .		2
39	All-Printed Paper Memory. ACS Nano, 2014, 8, 7613-7619.	14.6	137
40	Low operation voltage transparent resistive random access memory (T-RRAM) based on ultrathin a-TiOx films and its resistive switching characteristics. , 2014, , .		0
41	White Organic Light-Emitting Diode With Linearly Polarized Emission. IEEE Photonics Technology Letters, 2013, 25, 1321-1323.	2.5	19
42	Improved Performance of Plasmonic Thermal Emitter via Incorporation of Gold Nanoparticles. IEEE Photonics Technology Letters, 2013, 25, 1727-1730.	2.5	2
43	Graphene films grown at low substrate temperature and the growth model by using MBE technique. Journal of Crystal Growth, 2013, 378, 333-336.	1.5	2
44	Observation of room-temperature ballistic thermal conduction persisting over 8.3µm in SiGe nanowires. Nature Nanotechnology, 2013, 8, 534-538.	31.5	156
45	Enhanced Transmission of Higher Order Plasmon Modes With Random Au Nanoparticles in Periodic Hole Arrays. IEEE Photonics Technology Letters, 2013, 25, 47-50.	2.5	7
46	The operation principle of the well in quantum dot stack infrared photodetector. Journal of Applied Physics, 2013, 114, 244504.	2.5	3
47	Influence of the absorber layer thickness and rod length on the performance of three-dimensional nanorods thin film hydrogenated amorphous silicon solar cells. Journal of Applied Physics, 2013, 113, 163106.	2.5	7
48	Vorticity, gyroscopic precession, and spin-curvature force. Physical Review D, 2013, 87, .	4.7	17
49	Middle Infrared Radiation Induces G2/M Cell Cycle Arrest in A549 Lung Cancer Cells. PLoS ONE, 2013, 8, e54117.	2.5	27
50	Low-temperature grown graphene films by using molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	3.3	28
51	Two infrared emission modes with different wavelengths and orthogonal polarization in a waveguide thermal emitter. Journal of Applied Physics, 2012, 112, 074325.	2.5	2
52	Triple Peaks Plasmonic Thermal Emitter with Selectable Wavelength Using Periodic Block Pattern as Top Layer. IEEE Photonics Technology Letters, 2012, , .	2.5	3
53	Performance Improvement of AlGaAs/GaAs QWIP by \${m NH}_{3}\$ Plasma Treatment. IEEE Journal of Quantum Electronics, 2012, 48, 922-926.	1.9	7
54	A Special Issue for the Electrical Energy Storage and Conversion…. Journal of the Chinese Chemical Society, 2012, 59, 1159-1162.	1.4	0

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55	Nanoprojection Lithography Using Self-Assembled Interference Modules for Manufacturing Plasmonic Gratings. IEEE Photonics Technology Letters, 2012, 24, 1273-1275.	2.5	2
56	Linearly polarized light emission from organic light emitting diode with metallic nanograting structure. , 2012, , .		0
57	Plasmonic multilayer nanoparticles enhanced photocurrent in thin film hydrogenated amorphous silicon solar cells. Journal of Applied Physics, 2012, 112, .	2.5	25
58	Effect of Paired Apertures in a Periodic Hole Array on Higher Order Plasmon Modes. IEEE Photonics Technology Letters, 2012, 24, 2052-2055.	2.5	3
59	Painted graphitic carbon films formed underneath Ni templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 179-182.	0.8	0
60	Improved light scattering and surface plasmon tuning in amorphous silicon solar cells by double-walled carbon nanotubes. Solar Energy Materials and Solar Cells, 2012, 101, 200-203.	6.2	13
61	Investigating Far-Field Spectra and Near-Field Features of Extraordinary Optical Transmission Through Periodic U- to H-Shaped Apertures. IEEE Photonics Journal, 2012, 4, 387-398.	2.0	7
62	Two-color polarized infrared emission in a waveguide thermal emitter. , 2011, , .		0
63	Fabrication of morphology-tunable SiGe nanostructures grown on glass substrate. , 2011, , .		0
64	Improvement of heterojunction silicon solar cell efficiency by Au nanoparticles. , 2011, , .		0
65	Hydrogenated Amorphous Silicon Solar Cells on Textured Flexible Substrate Copied From a Textured Glass Substrate Template. IEEE Electron Device Letters, 2011, 32, 1254-1256.	3.9	12
66	Enhancement of localized resonance through non-centrosymmetric trumpet hole arrays in Ag/Si and Ag/SiO <inf>2</inf> /Ag structure. , 2011, , .		0
67	Localized shape resonance on silver film perforated by H-shaped and more complex shaped hole arrays. Optics Express, 2011, 19, 5225.	3.4	5
68	The effect of narrow bandwidth infrared radiation on the growth of Escherichia coli. Applied Physics Letters, 2011, 99, 163704.	3.3	8
69	Extraordinary transmission through a silver film perforated with bowtie-shaped aperture array in midinfrared region. Applied Physics Letters, 2011, 98, .	3.3	8
70	Triple peaks plasmonic thermal emitter with selectable wavelength using periodic block pattern as top layer. , 2011, , .		0
71	Wavelength selective plasmonic thermal emitter by polarization utilizing Fabry-Pérot type resonances. Applied Physics Letters, 2011, 98, .	3.3	24
72	Angle and polarization independent narrow-band thermal emitter made of metallic disk on SiO2. Applied Physics Letters, 2011, 98, .	3.3	41

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73	Self-Assembled Rippling Structure Based on Metal-Elastomer Composite for Tunable Plasmonics. IEEE Photonics Technology Letters, 2011, 23, 670-672.	2.5	2
74	Improved light scattering in amorphous silicon solar cell by double-walled carbon nanotubes. , 2011, ,		1
75	EVALUATION OF DUAL-SPECTRUM IR SPECTROGRAM SYSTEM ON INVASIVE DUCTAL CARCINOMA (IDC) BREAST CANCER. Biomedical Engineering - Applications, Basis and Communications, 2011, 23, 427-433.	0.6	4
76	Assessment of renewable energy reserves in Taiwan. Renewable and Sustainable Energy Reviews, 2010, 14, 2511-2528.	16.4	85
77	Hydrogenated amorphous silicon solar cell on glass substrate patterned by hexagonal nanocylinder array. Applied Physics Letters, 2010, 97, 193109.	3.3	21
78	The growth and radial analysis of Si/Ge core-shell nanowires. Applied Physics Letters, 2010, 97, 251912.	3.3	13
79	Narrow bandwidth and highly polarized ratio infrared thermal emitter. Applied Physics Letters, 2010, 97, 163112.	3.3	14
80	Optical characteristics of Al/Si structure and Ag/Al <inf>2</inf> 0 <inf>3</inf> /Ag plasmonic thermal emitter with square and hexagonal lattice. , 2010, , .		0
81	Narrow Bandwidth Midinfrared Waveguide Thermal Emitters. IEEE Photonics Technology Letters, 2010, 22, 1159-1161.	2.5	20
82	Extraordinary Transmission Through Ag–Si Structure Perforated With Rhombus Lattice Hole Arrays. IEEE Photonics Technology Letters, 2010, 22, 1482-1484.	2.5	1
83	Detection of Nighttime Melatonin Level in Chinese Original Quiet Sitting. Journal of the Formosan Medical Association, 2010, 109, 694-701.	1.7	14
84	A thermal emitter with selective wavelength: Based on the coupling between photonic crystals and surface plasmon polaritons. Journal of Applied Physics, 2009, 105, 033505.	2.5	10
85	Emission properties of Ag/dielectric/Ag plasmonic thermal emitter with different lattice type, hole shape, and dielectric material. Applied Physics Letters, 2009, 95, .	3.3	20
86	Characteristics of a waveguide mode in a trilayer Ag/SiO_2/Au plasmonic thermal emitter. Optics Letters, 2009, 34, 3089.	3.3	10
87	Effect of Wood's anomalies on the profile of extraordinary transmission spectra through metal periodic arrays of rectangular subwavelength holes with different aspect ratio. Optics Express, 2009, 17, 2631.	3.4	55
88	In(Ga)As Quantum Ring Terahertz Photodetector With Cutoff Wavelength at 175 \$mu\$m. IEEE Photonics Technology Letters, 2009, 21, 721-723.	2.5	11
89	Uniform Square Polycrystalline Silicon Fabricated by Employing Periodic Metallic Pads and SiON Absorption Layer for Thin Film Transistors. IEEE Transactions on Electron Devices, 2008, 55, 2212-2217.	3.0	0
90	Annealing Effect on the Formation of In(Ga)As Quantum Rings From InAs Quantum Dots. IEEE Photonics Technology Letters, 2008, 20, 165-167.	2.5	12

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91	Transition Mechanism of InAs Quantum Dot to Quantum Ring Revealed by Photoluminescence Spectra. IEEE Photonics Technology Letters, 2008, 20, 1372-1374.	2.5	9
92	Surface plasmon on aluminum concentric rings arranged in a long-range periodic structure. Applied Physics Letters, 2008, 92, 253111.	3.3	10
93	Coupling of surface plasmons between two silver films in a Ag/SiO2/Ag plasmonic thermal emitter with grating structure. Applied Physics Letters, 2008, 93, .	3.3	28
94	Enhancement of Thermal Radiation in Plasmonic Thermal Emitter by Surface Plasmon Resonance. , 2008, , .		3
95	Localized surface plasmon polaritons in Agâ^•SiO2â^•Ag plasmonic thermal emitter. Applied Physics Letters, 2008, 93, .	3.3	49
96	Voltage-Tunable Dual-Band In(Ga)As Quantum-Ring Infrared Photodetector. IEEE Photonics Technology Letters, 2007, 19, 1511-1513.	2.5	10
97	Dispersion relation of Alâ^•Si surface plasmon in hexagonally ordered aluminum hole arrays. Journal of Applied Physics, 2007, 101, 054305.	2.5	16
98	Coupling of surface plasmons between two silver films in a plasmonic thermal emitter. Applied Physics Letters, 2007, 91, .	3.3	22
99	Reflection and emission properties of an infrared emitter. Optics Express, 2007, 15, 14673.	3.4	57
100	Extraordinary transmission through aluminum metal with superperiodic micro-cell arranged in a long-range periodic structure. , 2007, , .		0
101	Low Temperature Polycrystalline Silicon TFTs on Polyimide and Glass Substrates. , 2007, , .		3
102	Infrared Plasmonic Thermal Emitter and Its Application in Biological System. , 2007, , .		1
103	Silicon nanowires synthesized by vapor–liquid–solid growth on excimer laser annealed thin gold film. Journal of Nanoparticle Research, 2007, 9, 657-660.	1.9	7
104	Dispersion of surface plasmon polaritons on silver film with rectangular hole arrays in a square lattice. Applied Physics Letters, 2006, 89, 093102.	3.3	31
105	Extraordinary transmission through Al metal with periodic micro-cell holes arranged in the random structure. , 2006, , .		0
106	Bragg scattering of surface plasmon polaritons on extraordinary transmission through silver periodic perforated hole arrays. Applied Physics Letters, 2006, 88, 213112.	3.3	32
107	Two Color Squared-lattice Plasmonic Thermal Emitter. , 2006, , .		0
108	High-temperature operation normal incident 256/spl times/256 InAs-GaAs quantum-dot infrared photodetector focal plane array. IEEE Photonics Technology Letters, 2006, 18, 986-988.	2.5	61

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109	High performance midinfrared narrow-band plasmonic thermal emitter. Applied Physics Letters, 2006, 89, 173116.	3.3	111
110	Opto-electronic Properties of InGaAs Quantum Ring Infrared Photodetectors. , 2006, , .		0
111	The Influence of B2H6 on the Growth of Silicon Nanowire. Journal of Nanoparticle Research, 2005, 7, 615-620.	1.9	6
112	Large Grain Poly-Si>tex<\$(sim rm 10~muhbox m)\$>/tex <tfts by="" excimer="" laser<br="" prepared="">Annealing Through a Thick SiON Absorption Layer. IEEE Transactions on Electron Devices, 2004, 51, 166-171.</tfts>	3.0	7
113	Growth of InGaAs-capped InAs quantum dots characterized by Atomic Force Microscope and Scanning Electron Microscope. Journal of Nanoparticle Research, 2004, 6, 407-410.	1.9	6
114	The structural and optical properties of gallium arsenic nanoparticles. Journal of Nanoparticle Research, 2004, 6, 415-419.	1.9	8
115	The fabrication of polysilicon thin film transistors by copper-induced lateral crystallization. IEEE Transactions on Electron Devices, 2003, 50, 816-821.	3.0	11
116	Transport characteristics of InAs/GaAs quantum-dot infrared photodetectors. Applied Physics Letters, 2003, 83, 752-754.	3.3	20
117	Stability improvement of deuterated amorphous silicon thin-film transistors characterized by modified Schottky-contact gated-four-probe method. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003. 21. 677.	1.6	7
118	InAs/GaAs quantum dot infrared photodetector (QDIP) with double Al/sub 0.3/Ga/sub 0.7/As blocking barriers. IEEE Transactions on Electron Devices, 2002, 49, 1341-1347.	3.0	33
119	Near-room-temperature operation of an InAs/GaAs quantum-dot infrared photodetector. Applied Physics Letters, 2001, 78, 2428-2430.	3.3	142
120	Improvement of current leakage in the InAs photodetector by molecular beam epitaxy. Journal of Crystal Growth, 2001, 227-228, 167-171.	1.5	12
121	Title is missing!. Journal of Nanoparticle Research, 2001, 3, 489-492.	1.9	5
122	Hydrogenated amorphous silicon-germanium PIN X-ray detector. IEEE Transactions on Electron Devices, 2001, 48, 1564-1567.	3.0	9
123	High-performance InAs/GaAs quantum-dot infrared photodetectors with a single-sided Al0.3Ga0.7As blocking layer. Applied Physics Letters, 2001, 78, 2784-2786.	3.3	61
124	Improved stability of deuterated amorphous silicon thin film transistors. Journal of Applied Physics, 1999, 85, 543-550.	2.5	13
125	Amorphous-silicon thin-film transistor with liquid phase deposition of silicon dioxide gate insulator. IEEE Electron Device Letters, 1999, 20, 138-139.	3.9	8
126	High field effect mobility deuterated amorphous silicon thin-film transistors based on the substitution of hydrogen with deuterium. IEEE Electron Device Letters, 1999, 20, 415-417.	3.9	1

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127	The retardation of aluminum-amorphous silicon interaction by phosphine plasma treatment. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 587-589.	2.1	5
128	Structural, optical, and electrical properties of hydrogenated amorphous silicon germanium alloys. Journal of Applied Physics, 1998, 83, 4111-4123.	2.5	84
129	Interfacial interaction between Al-1%Si and phosphorus-doped hydrogenated amorphous Si alloy at low temperature. Journal of Applied Physics, 1997, 81, 7793-7797.	2.5	8
130	A possible mechanism for improved light-induced degradation in deuterated amorphous-silicon alloy. Applied Physics Letters, 1997, 71, 1498-1500.	3.3	40
131	Room temperature unpassivated InAs p-i-n photodetectors grown by molecular beam epitaxy. IEEE Transactions on Electron Devices, 1997, 44, 209-213.	3.0	33
132	Application of liquid phase deposited silicon dioxide to metal-oxide-semiconductor capacitor and amorphous silicon thin-film transistor. IEEE Transactions on Electron Devices, 1996, 43, 599-604.	3.0	10
133	An InSb integrated photo-MOSFET fabricated by photo-enhanced chemical vapour deposition. Optical and Quantum Electronics, 1996, 28, 1277-1286.	3.3	0
134	Active hollow four quadrant orientation detector array for application to pattern recognition. IEEE Transactions on Electron Devices, 1995, 42, 1233-1239.	3.0	3
135	Planarization of amorphous silicon thin film transistors by liquid phase deposition of silicon dioxide. IEEE Transactions on Electron Devices, 1995, 42, 1918-1923.	3.0	8
136	Detailed investigation of InSb p-channel metal-oxide-semiconductor field effect transistor prepared by photo-enhanced chemical vapor deposition. IEEE Transactions on Electron Devices, 1995, 42, 795-803.	3.0	2
137	The hydrogenated amorphous silicon active hollow four quadrant orientation detector for application to neural network image sensors. IEEE Transactions on Electron Devices, 1994, 41, 666-670.	3.0	10
138	High Gain Npn AlGaAs/GaAs Heterojunction Bipolar Transistors Prepared by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1992, 31, L385-L387.	1.5	1
139	High-performance a-Si:H thin-film transistor using lightly doped channel. IEEE Transactions on Electron Devices, 1991, 38, 676-678.	3.0	7
140	Amorphous-silicon thin-film transistors with very high field-effect mobility. IEEE Electron Device Letters, 1991, 12, 120-121.	3.9	16
141	Effect of Emitted Bioenergy on Biochemical Functions of Cells. The American Journal of Chinese Medicine, 1991, 19, 285-292.	3.8	41
142	The Origin Of Instability In Metal/SiO 2 /InSb Capacitor Fabricated By Photo-Enhanced Chemical Vapor Deposition. , 1989, 1107, 176.		0
143	The hot electron effect in double heterojunction bipolar transistors: Theory and experiment. Solid-State Electronics, 1988, 31, 1653-1656.	1.4	2
144	An amorphous SiC/Si two-color detector. IEEE Electron Device Letters, 1987, 8, 365-367.	3.9	36

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145	Engineering On NPN AlGaAs Heterojunction Bipolar Transistors. Proceedings of SPIE, 1987, , .	0.8	0
146	AlGaAs/GaAs visible ridge waveguide laser with multicavity structure. IEEE Journal of Quantum Electronics, 1987, 23, 1283-1286.	1.9	2
147	The amorphous SiC/Si two and three-color detector with high rejection ratio. , 1987, , .		0
148	The effect of the base—collector potential spike on the common-emitter l—V characteristics of AlGaAs double-heterojunction bipolar transistors. IEEE Transactions on Electron Devices, 1987, 34, 1463-1469.	3.0	25
149	"Band readjustment" effect with applications to solar cells. IEEE Transactions on Electron Devices, 1980, 27, 844-850.	3.0	7
150	A new process for liquid phase deposition of silicon oxide and its application in amorphous silicon thin film transisitor. , 0, , .		0
151	The electrical and optical properties of implanted amorphous silicon. , 0, , .		0
152	Identification of tunneling peaks in the GaAs/AlAs/GaAs resonant tunneling diode by magnetic fields. , 0, , .		0
153	Radiation hardness of fluorinated oxides prepared by liquid phase deposition method following rapid thermal oxidation. , 0, , .		1
154	Active hollow four quadrant orientation detector array for applications to pattern recognition. , 0, , .		0
155	A novel angle position detector for application to pattern recognition. , 0, , .		0
156	High temperature operated (â^1⁄4250 K) photovoltaic-photoconductive (PV-PC) mixed-mode InAs/GaAs quantum dot infrared photodetector. , 0, , .		2
157	Temperature-stable (wavelength â^1⁄4 1 Î1⁄4m) InAs/GaAs quantum dot light-emitting diode. , 0, , .		0
158	Phase separation growth of InGaAs cap layer on InAs/GaAs quantum dots. , 0, , .		0
159	The growth and Raman spectra of boron-doped silicon nanowires. , 0, , .		0
160	Optical properties of self-assembled InGaAs quantum wires grown on [100] GaAs substrate. , 0, , .		0
161	Switching between transverse electric and magnetic mode in InAs/AlGaAs/GaAs quantum dot infrared photodetector. , 0, , .		0
162	Two Color Squared-lattice Plasmonic Thermal Emitter. , 0, , .		0

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163	Extraordinary transmission through Al metal with periodic micro-cell holes arranged in the random structure. , 0, , .		Ο
164	Opto-electronic Properties of InGaAs Quantum Ring Infrared Photodetectors. , 0, , .		0
165	Correlation between Pineal Activation and Religious Meditation Observed by Functional Magnetic Resonance Imaging. Nature Precedings, 0, , .	0.1	4
166	Radiation hardness of fluorinated oxides prepared by liquid phase deposition method following rapid thermal oxidation. , 0, , .		0
167	Identification of tunneling peaks in the GaAs/AlAs/GaAs resonant tunneling diode by magnetic fields. , 0, , .		0
168	Excimer laser annealing process for polysilicon TFT on glass and plastic substrates. , 0, , .		0